

**AMENDMENTS TO THE CLAIMS:**

*Please amend the claims as follows:*

1-13. (Cancelled)

14. (Currently amended) A semiconductor device comprising a MOS transistor with a plurality of gate electrodes,

wherein the gate electrodes are formed on a semiconductor substrate having a silicon layer at least in the surface thereof,

the MOS transistor has a gate length of 0.15  $\mu\text{m}$  or smaller and is formed in an element region surrounded with an isolation insulating film,

each of the gate electrodes is arranged between ~~the other gate electrodes or between one of the other electrodes and a dummy~~ patterns pattern with a space left from each side thereof,

sidewalls are provided on side walls of each of the gate electrodes ~~and on side walls of another said gate electrode,~~

a first silicide layer is formed in the upper portion of the gate electrode,

a second silicide layer is formed in a portion of the semiconductor substrate surface which is located in part of the element region between the gate electrode and ~~at least one of another gate electrode and the dummy~~ patterns pattern, and

the first silicide layer has a greater thickness than the second silicide layer, and

one of the dummy patterns is a dummy gate electrode which is an electrode pattern having the shape of a gate electrode, and the other dummy pattern is a pattern made of insulating material.

15. (Currently amended) The device of claim 14, wherein the ~~dummy pattern is a dummy gate electrode which is an electrode pattern having the shape of a gate electrode, and the dummy pattern~~ is an electrode which is not electrically connected to a semiconductor integrated circuit of the semiconductor device.

16. (Cancelled)

17. (Currently amended) The device of claim 14, wherein the ~~dummy pattern is either a pattern made of a dummy gate electrode which is an electrode pattern having the shape of a gate electrode with side walls of the dummy pattern~~ is provided with sidewalls on its side walls and is not electrically connected to a semiconductor integrated circuit of the semiconductor device.

18. (Currently amended) The device of claim ~~[[16]]~~ 14, wherein the pattern made of insulating material is formed on the isolation insulating film.

19-25. (Cancelled)